



12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20181011000.1

**Qualification of RFAB as an additional Wafer Fab Site option for select devices
Change Notification / Sample Request**

Date: October 15, 2018

To: TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN_ww_admin_team@list.ti.com).

PCN Team
SC Business Services



20181011000.1
Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
DRV401AIRGWR	null
DRV401AIDWPR	null

Technical details of this Product Change follow on the next page(s).

PCN Number:	20181011000.1		PCN Date:	Oct 15, 2018																						
Title:	Qualification of RFAB as an additional Wafer Fab Site option for select devices in HPA07 Technology																									
Customer Contact:	PCN Manager		Dept:	Quality Services																						
Proposed 1st Ship Date:	Jan 15, 2019		Estimated Sample Availability:	Date provided at sample request.																						
Change Type:																										
<input type="checkbox"/> Assembly Site	<input type="checkbox"/> Assembly Process	<input type="checkbox"/> Assembly Materials																								
<input type="checkbox"/> Design	<input type="checkbox"/> Electrical Specification	<input type="checkbox"/> Mechanical Specification																								
<input type="checkbox"/> Test Site	<input type="checkbox"/> Packing/Shipping/Labeling	<input type="checkbox"/> Test Process																								
<input type="checkbox"/> Wafer Bump Site	<input type="checkbox"/> Wafer Bump Material	<input type="checkbox"/> Wafer Bump Process																								
<input checked="" type="checkbox"/> Wafer Fab Site	<input checked="" type="checkbox"/> Wafer Fab Materials	<input type="checkbox"/> Wafer Fab Process																								
	<input type="checkbox"/> Part number change																									
PCN Details																										
Description of Change:																										
Texas Instruments is pleased to announce the qualification of its RFAB fabrication facility as an additional Wafer Fab source for the selected devices listed in "Product Affected" section.																										
<table border="1" style="width: 100%;"> <thead> <tr> <th colspan="3">Current Sites</th> <th colspan="3">Additional Sites</th> </tr> <tr> <th>Current Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> <th>Additional Fab Site</th> <th>Process</th> <th>Wafer Diameter</th> </tr> </thead> <tbody> <tr> <td>DP1DM5</td> <td>HPA07</td> <td>200mm</td> <td rowspan="2">RFAB</td> <td rowspan="2">HPA07</td> <td rowspan="2">300mm</td> </tr> <tr> <td>AIZU</td> <td>HPA07</td> <td>200mm</td> </tr> </tbody> </table>						Current Sites			Additional Sites			Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	DP1DM5	HPA07	200mm	RFAB	HPA07	300mm	AIZU	HPA07	200mm
Current Sites			Additional Sites																							
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DP1DM5	HPA07	200mm	RFAB	HPA07	300mm																					
AIZU	HPA07	200mm																								
Qual details are provided in the Qual Data Section.																										
Reason for Change:																										
Continuity of Supply																										
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):																										
None																										
Changes to product identification resulting from this PCN:																										
Current																										
Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City																							
DP1DM5	DM5	USA	Dallas																							
AIZU	CU2	JPN	Aizuwakamatsu-shi																							
New Fab Site																										
Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City																							
RFAB	RFB	USA	Richardson																							
Sample product shipping label (not actual product label)																										
<div style="display: flex; align-items: flex-start;"> <div style="flex: 1;">  <p>TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20:</p> <table border="1" style="font-size: small;"> <tr> <td>MSL '2 / 260C / 1 YEAR</td> <td>SEAL DT</td> </tr> <tr> <td>MSL 1 / 235C / UNLIM</td> <td>03/29/04</td> </tr> </table> <p>OPT: 39 ITEM: 39 LBL: 5A (L)T0:1750</p> </div> <div style="flex: 1; text-align: center;">  </div> <div style="flex: 2;"> <p>(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T) LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (P) (2P) REV: (V) 0033317 (20L) CS0: SHE (21L) CCO: USA (22L) AS0: MLA (23L) ACO: MYS</p> </div> </div>						MSL '2 / 260C / 1 YEAR	SEAL DT	MSL 1 / 235C / UNLIM	03/29/04																	
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MSL 1 / 235C / UNLIM	03/29/04																									
Product Affected Group:																										
DRV401AIDWP	DRV401AIDWPRG4	DRV401AIRGWT	DRV401AIRGWTG4																							
DRV401AIDWPR	DRV401AIRGWR																									

Qualification Report
RFAB G4DRV401GAP offload from Aizu DRV401AIRGWR
Approve Date 28-Sept-2018
Product Attributes

Attributes	Qual Device: DRV401AIRGWR	Process QBS Device: CD3232A1YFFR -	Package QBS Device: DRV401AIRGWR	Package QBS Device: BQ24196RGER
Wafer Fab Supplier	RFAB	RFAB	Aizu	RFAB
Wafer Process	HPA07	HPA07	HPA07	LBC7
Assembly Site	CDAT	JCAP	CDAT	CDAT
Package Type	VQFN	WCSP	VQFN	WSON
Package Designator	RGW	YFF	RGW	DRV

- Qual Devices qualified at LEVEL2-260CG: DRV401AIRGWR

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	Test Name / Condition	Duration	Qual Device: DRV401AIRGWR	Process QBS Device: CD3232A1YFFR -	Package QBS Device: DRV401AIRGWR	Package QBS Device: BQ24196RGER
HAST	Biased HAST, 130C/85%RH	96 Hours	-	3/231/0	-	3/231/0
UHAST	Unbiased HAST 130C/85%RH	96 Hours	-	3/231/0	-	-
AC	Autoclave 121C	96 Hours	-	-	3/231/0	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	-	3/231/0	3/231/0	-
HTSL	High Temp. Storage Bake, 170C	420 Hours	-	3/231/0	3/231/0	-
HTOL	Life Test, 125C	1000 Hours	2/154/0	3/231/0	-	-
ELFR	Early Life Failure Rate, 150C	24 Hours	-	3/2400/0	-	-
HBM	ESD - HBM	1500 V	1/3/0	3/9/0	-	-
HBM	ESD - HBM	1000 V	1/3/0	-	-	-
CDM	ESD - CDM	1000 V	1/3/0	3/9/0	-	-
LU	Latch-up	(Per AEC Q100-004)	1/6/0	3/18/0	-	-
ED	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	1/30/0	3/90/0	-	-
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass	Pass	-	-
MQ	Manufacturability (Wafer Fab)	(per mfg. Site specification)	Pass	Pass	-	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com